

## **KSB817**

## Audio Power Amplifier Car Booster Output Amplifier DC to DC Converter

- High Current Capability
- High Power Dissipation
- Complementary to KSD1047



## **PNP Planar Silicon Transistor**

## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	- 160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 140	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 6	V
I <sub>C</sub>	Collector Current (DC)	- 8	Α
I <sub>CP</sub>	*Collector Current (Pulse)	- 16	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	80	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 40 ~ 150	°C

## Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = -5 \text{mA}, I_{E} = 0$	- 160			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -10 \text{mA}, I_B = 0$	- 140			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -5 \text{mA}, I_C = 0$	-6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -80V, I_{E} = 0$			- 0.1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -4V, I_{C} = 0$			- 0.1	mA
h <sub>FE1</sub> h <sub>FE2</sub>	* DC Current Gain	$V_{CE} = -5V, I_{C} = -1A$ $V_{CE} = -5V, I_{C} = -6A$	60 20		200	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A, I <sub>B</sub> = -0.5A			- 2.5	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	V <sub>CE</sub> = - 5V, I <sub>C</sub> = - 1A			- 1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = - 5V, I <sub>C</sub> = - 1A		15		MHz
f <sub>T</sub> C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = - 10V, f = 1MHz		300		pF
t <sub>ON</sub>	Turn ON Time	V <sub>CC</sub> = 20V		0.25		μs
t <sub>F</sub>	Fall Time	$I_C = 1A = 10 \cdot I_{B1} = -10 \cdot I_{B2}$		0.53		μs
t <sub>STG</sub>	Storage Time	$R_L = 20\Omega$		1.61		μs

### \* Pulse Test: PW = 20μs

## **h**<sub>FE</sub> Classificntion

Classification	0	Y
h <sub>FE1</sub>	60 ~ 120	100 ~ 200

# **Typical Characteristics**

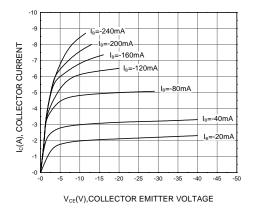


Figure 1. Static Characteristic

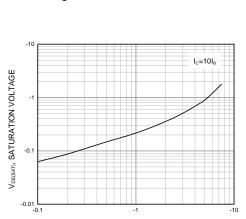


Figure 3. Collector-Emitter Saturation Voltage

I<sub>C</sub>(A) COLLECTOR CURRENT

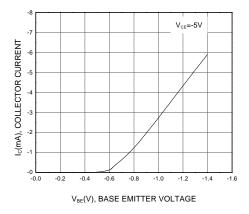


Figure 5. Base-Emitter On Voltage

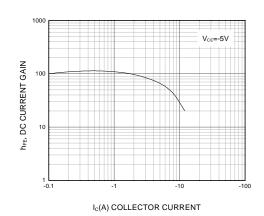


Figure 2. DC current Gain

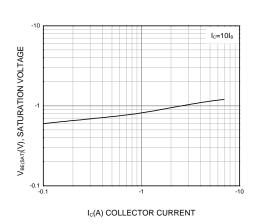


Figure 4. Base-Emitter Saturation Voltage

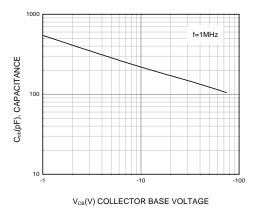


Figure 6. Collector Output Capacitance

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# Typical Characteristics (Continued)

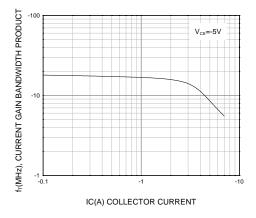


Figure 7. Current Gain Bandwidth Product

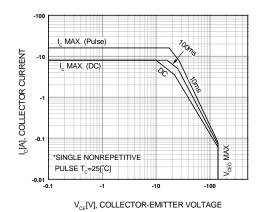


Figure 8. Safe Operating Area

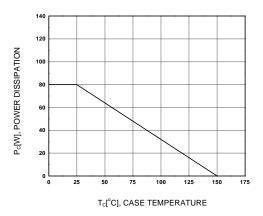
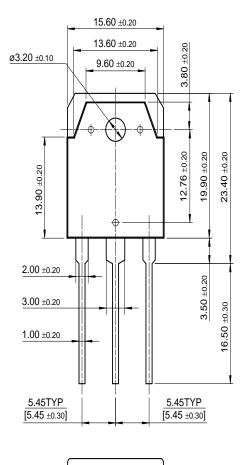


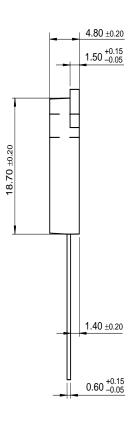
Figure 9. Current Gain Bandwidth Product

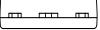
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# **Package Demensions**

TO-3P







Dimensions in Millimeters

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